

FEATURES

- ±2 V to ±6 V dual supply
- 2 V to 12 V single supply
- Automotive temperature range –40°C to +125°C
- <0.1 nA leakage currents
- 45 Ω on resistance over full signal range
- Rail-to-rail switching operation
- Single 8-to-1 multiplexer ADG658
- Differential 4-to-1 multiplexer ADG659
- 16-lead LFCSP/TSSOP/QSOP packages
- Typical power consumption <0.1 μW
- TTL/CMOS compatible inputs
- Package upgrades to 74HC4051/74HC4052 and
MAX4051/MAX4052/MAX4581/MAX4582

APPLICATIONS

- Automotive applications
- Automatic test equipment
- Data acquisition systems
- Battery-powered systems
- Communication systems
- Audio and video signal routing
- Relay replacement
- Sample-and-hold systems
- Industrial control systems

GENERAL DESCRIPTION

The ADG658 and ADG659 are low voltage, CMOS analog multiplexers comprised of eight single channels and four differential channels, respectively. The ADG658 switches one of eight inputs (S1–S8) to a common output, D, as determined by the 3-bit binary address lines A0, A1, and A2. The ADG659 switches one of four differential inputs to a common differential output, as determined by the 2-bit binary address lines A0 and A1. An $\overline{\text{EN}}$ input on both devices is used to enable or disable the device. When disabled, all channels are switched off.

These parts are designed on an enhanced process that provides lower power dissipation yet gives high switching speeds. These parts can operate equally well as either multiplexers or demultiplexers and have an input range that extends to the supplies. All channels exhibit break-before-make switching action, preventing momentary shorting when switching channels. All digital inputs have 0.8 V to 2.4 V logic thresholds, ensuring TTL/CMOS logic compatibility when using single +5 V or dual ±5 V supplies.

FUNCTIONAL BLOCK DIAGRAM

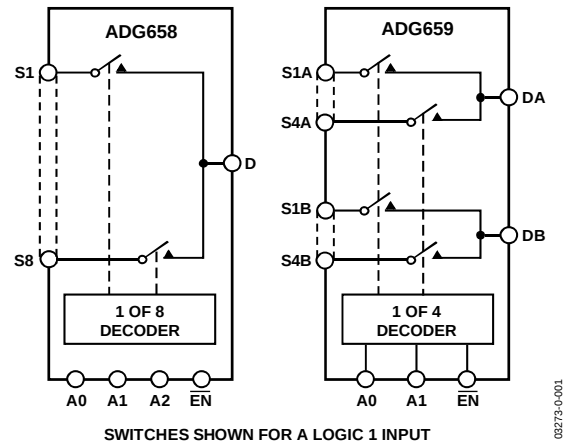


Figure 1.

The ADG658 and ADG659 are available in 16-lead TSSOP/QSOP packages and 16-lead 4 mm × 4 mm LFCSP packages.

PRODUCT HIGHLIGHTS

1. Single- and dual-supply operation. The ADG658 and ADG659 offer high performance and are fully specified and guaranteed with ±5 V, +5 V, and +3 V supply rails.
2. Automotive temperature range –40°C to +125°C.
3. Low power consumption, typically <0.1 μW.
4. 16-lead 4 mm × 4 mm LFCSP packages, 16-lead TSSOP package and 16-lead QSOP package.

Rev. B

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TABLE OF CONTENTS

Features	1	Absolute Maximum Ratings	9
Applications	1	ESD Caution.....	9
Functional Block Diagram	1	Pin Configurations and Function Descriptions	11
General Description	1	Typical Performance Characteristics	13
Product Highlights	1	Test Circuits.....	16
Revision History	2	Outline Dimensions	19
Specifications.....	3	Ordering Guide.....	20
Dual Supply	3		
5 V Single Supply.....	5		
2.7 V to 3.6 V Single Supply	7		

REVISION HISTORY

2/09—Rev. A to Rev. B	
Changes to Ordering Guide	20
7/04—Rev. 0 to Rev. A	
Updated Format.....	Universal
Added QSOP Package Outline	20
Changes to Ordering Guide	20
3/03—Rev. 0: Initial Version	

SPECIFICATIONS

DUAL SUPPLY

$V_{DD} = +5\text{ V} \pm 10\%$, $V_{SS} = -5\text{ V} \pm 10\%$, GND = 0 V, unless otherwise noted.

Table 1.

Parameter	+25°C	B Version –40°C to +85°C	Y Version –40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V_{SS} to V_{DD}	V	$V_{DD} = +4.5\text{ V}$, $V_{SS} = -4.5\text{ V}$
On Resistance (R_{ON})	45			Ω typ	$V_S = \pm 4.5\text{ V}$, $I_S = 1\text{ mA}$; see Figure 21
	75	90	100	Ω max	
On Resistance Match between Channels (ΔR_{ON})	1.3			Ω typ	$V_S = 3.5\text{ V}$, $I_S = 1\text{ mA}$
	3	3.2	3.5	Ω max	$V_{DD} = +5\text{ V}$, $V_{SS} = -5\text{ V}$;
On Resistance Flatness ($R_{FLAT(ON)}$)	10			Ω typ	$V_S = \pm 3\text{ V}$, $I_S = 1\text{ mA}$
	16	17	18	Ω max	
LEAKAGE CURRENTS					
Source OFF Leakage I_S (OFF)	± 0.005			nA typ	$V_{DD} = +5.5\text{ V}$, $V_{SS} = -5.5\text{ V}$
	± 0.2		± 5	nA max	$V_D = \pm 4.5\text{ V}$, $V_S = \mp 4.5\text{ V}$; see Figure 22
Drain OFF Leakage I_D (OFF)	± 0.005			nA typ	$V_D = \pm 4.5\text{ V}$, $V_S = \mp 4.5\text{ V}$; see Figure 23
ADG658	± 0.2		± 5	nA max	
ADG659	± 0.1		± 2.5	nA max	
Channel ON Leakage I_D , I_S (ON)	± 0.005			nA typ	$V_D = V_S = \pm 4.5\text{ V}$; see Figure 24
ADG658	± 0.2		± 5	nA max	
ADG659	± 0.1		± 2.5	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.4	V min	
Input Low Voltage, V_{INL}			0.8	V max	
Input Current					
I_{INL} or I_{INH}	0.005			μA typ	$V_{IN} = V_{INL}$ or V_{INH}
			± 1	μA max	
C_{IN} , Digital Input Capacitance	2			pF typ	
DYNAMIC CHARACTERISTICS¹					
$t_{TRANSITION}$	80			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	115	140	165	ns max	$V_S = 3\text{ V}$; see Figure 25
$t_{ON}(\overline{EN})$	80			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	115	140	165	ns max	$V_S = 3\text{ V}$; see Figure 27
$t_{OFF}(\overline{EN})$	30			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	45	50	55	ns max	$V_S = 3\text{ V}$; see Figure 27
Break-Before-Make Time Delay, t_{BBM}	50			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
			10	ns min	$V_{S1} = V_{S2} = 3\text{ V}$; see Figure 26
Charge Injection	2			pC typ	$V_S = 0\text{ V}$, $R_S = 0\ \Omega$,
	4			pC max	$C_L = 1\text{ nF}$; see Figure 28
Off Isolation	–90			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 29
Total Harmonic Distortion, THD + N	0.025			% typ	$R_L = 600\ \Omega$, 2 V p-p, $f = 20\text{ Hz}$ to 20 kHz
Channel-to-Channel Crosstalk (ADG659)	–90			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 31
–3 dB Bandwidth					
ADG658	210			MHz typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 30
ADG659	400			MHz typ	

ADG658/ADG659

Parameter	+25°C	B Version –40°C to +85°C	Y Version –40°C to +125°C	Unit	Test Conditions/Comments
C _S (OFF)	4			pF typ	f = 1 MHz
C _D (OFF)					
ADG658	23			pF typ	f = 1 MHz
ADG659	12			pF typ	f = 1 MHz
C _D , C _S (ON)					
ADG658	28			pF typ	f = 1 MHz
ADG659	16			pF typ	f = 1 MHz
POWER REQUIREMENTS					
I _{DD}	0.01			μA typ	V _{DD} = +5.5 V, V _{SS} = –5.5 V
			1	μA max	Digital Inputs = 0 V or 5.5 V
I _{SS}	0.01			μA typ	Digital Inputs = 0 V or 5.5 V
			1	μA max	

¹ Guaranteed by design; not subject to production test.

5 V SINGLE SUPPLY

$V_{DD} = 5\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $GND = 0\text{ V}$, unless otherwise noted.

Table 2.

Parameter	+25°C	B Version –40°C to +85°C	Y Version –40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 to V_{DD}	V	$V_{DD} = 4.5\text{ V}$, $V_{SS} = 0\text{ V}$
On Resistance (R_{ON})	85			Ω typ	$V_S = 0\text{ V}$ to 4.5 V , $I_S = 1\text{ mA}$; see Figure 21
	150	160	200	Ω max	
On Resistance Match between Channels (ΔR_{ON})	4.5			Ω typ	$V_S = 3.5\text{ V}$, $I_S = 1\text{ mA}$
	8	9	10	Ω max	
On Resistance Flatness ($R_{FLAT(ON)}$)	13	14	16	Ω typ	$V_{DD} = 5\text{ V}$, $V_{SS} = 0\text{ V}$, $V_S = 1.5\text{ V}$ to 4 V , $I_S = 1\text{ mA}$
LEAKAGE CURRENTS					
Source OFF Leakage I_S (OFF)	± 0.005			nA typ	$V_{DD} = 5.5\text{ V}$
	± 0.2		± 5	nA max	$V_S = 1\text{ V}/4.5\text{ V}$, $V_D = 4.5\text{ V}/1\text{ V}$; see Figure 22
Drain OFF Leakage I_D (OFF)	± 0.005			nA typ	$V_S = 1\text{ V}/4.5\text{ V}$, $V_D = 4.5\text{ V}/1\text{ V}$; see Figure 23
ADG658	± 0.2		± 5	nA max	
ADG659	± 0.1		± 2.5	nA max	
Channel ON Leakage I_D , I_S (ON)	± 0.005			nA typ	$V_S = V_D = 1\text{ V}$ or 4.5 V , see Figure 24
ADG658	± 0.2		± 5	nA max	
ADG659	± 0.1		± 2.5	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.4	V min	
Input Low Voltage, V_{INL}			0.8	V max	
Input Current I_{INL} or I_{INH}	0.005			μA typ	$V_{IN} = V_{INL}$ or V_{INH}
			± 1	μA max	
C_{IN} , Digital Input Capacitance	2			pF typ	
DYNAMIC CHARACTERISTICS¹					
$t_{TRANSITION}$	120			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	200	270	300	ns max	$V_S = 3\text{ V}$; see Figure 25
$t_{ON}(\overline{EN})$	120			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	190	245	280	ns max	$V_S = 3\text{ V}$; see Figure 27
$t_{OFF}(\overline{EN})$	35			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	50	60	70	ns max	$V_S = 3\text{ V}$; see Figure 27
Break-Before-Make Time Delay, t_{BBM}	100			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
			10	ns min	$V_{S1} = V_{S2} = 3\text{ V}$; see Figure 26
Charge Injection	0.5			pC typ	$V_S = 2.5\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$; see Figure 28
	1			pC max	
Off Isolation	–90			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 29
Channel-to-Channel Crosstalk (ADG659)	–90			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; $f = 1\text{ MHz}$; see Figure 31
–3 dB Bandwidth					
ADG658	180			MHz typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 30
ADG659	330			MHz typ	
C_S (OFF)	5			pF typ	$f = 1\text{ MHz}$
C_D (OFF)					
ADG658	29			pF typ	$f = 1\text{ MHz}$
ADG659	15			pF typ	$f = 1\text{ MHz}$

ADG658/ADG659

Parameter	+25°C	B Version –40°C to +85°C	Y Version –40°C to +125°C	Unit	Test Conditions/Comments
C _D , C _S (ON)					
ADG658	30			pF typ	f = 1 MHz
ADG659	16			pF typ	f = 1 MHz
POWER REQUIREMENTS					V _{DD} = 5.5 V
I _{DD}	0.01		1	μA typ μA max	Digital Inputs = 0 V or 5.5 V

¹ Guaranteed by design; not subject to production test.

2.7 V TO 3.6 V SINGLE SUPPLY

$V_{DD} = 2.7$ to 3.6 V, $V_{SS} = 0$ V, GND = 0 V, unless otherwise noted.

Table 3.

Parameter	+25°C	B Version –40°C to +85°C	Y Version –40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 to V_{DD}	V	$V_{DD} = 2.7$ V, $V_{SS} = 0$ V
On Resistance (R_{ON})	185			Ω typ	$V_S = 0$ V to 2.7 V, $I_S = 0.1$ mA; see Figure 21
	300	350	400	Ω max	
On Resistance Match between	2			Ω typ	$V_S = 1.5$ V, $I_S = 0.1$ mA
Channels (ΔR_{ON})	4.5	6	7	Ω max	
LEAKAGE CURRENTS					
Source OFF Leakage I_S (OFF)	± 0.005			nA typ	$V_{DD} = 3.3$ V
	± 0.2		± 5	nA max	$V_S = 1$ V/3 V, $V_D = 3$ V/1 V; see Figure 22
Drain OFF Leakage I_D (OFF)	± 0.005			nA typ	$V_S = 1$ V/3 V, $V_D = 3$ V/1 V; see Figure 23
ADG658	± 0.2		± 5	nA max	
ADG659	± 0.1		± 2.5	nA max	
Channel ON Leakage I_D, I_S (ON)	± 0.005			nA typ	$V_S = V_D = 1$ V or 3 V, see Figure 24
ADG658	± 0.2		± 5	nA max	
ADG659	± 0.1		± 2.5	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.0	V min	
Input Low Voltage, V_{INL}			0.5	V max	
Input Current					
I_{INL} or I_{INH}	0.005			μ A typ	$V_{IN} = V_{INL}$ or V_{INH}
			± 1	μ A max	
C_{IN} , Digital Input Capacitance	2			pF typ	
DYNAMIC CHARACTERISTICS¹					
$t_{TRANSITION}$	200			ns typ	$R_L = 300$ Ω , $C_L = 35$ pF
	370	440	490	ns max	$V_S = 1.5$ V; see Figure 25
$t_{ON}(\overline{EN})$	230			ns typ	$R_L = 300$ Ω , $C_L = 35$ pF
	370	440	490	ns max	$V_S = 1.5$ V; see Figure 27
$t_{OFF}(\overline{EN})$	50			ns typ	$R_L = 300$ Ω , $C_L = 35$ pF
	80	90	110	ns max	$V_S = 1.5$ V; see Figure 27
Break-Before-Make Time Delay, t_{BBM}	200			ns typ	$R_L = 300$ Ω , $C_L = 35$ pF
			10	ns min	$V_{S1} = V_{S2} = 1.5$ V; see Figure 26
Charge Injection	1			pC typ	$V_S = 1.5$ V, $R_S = 0$ Ω , $C_L = 1$ nF; see Figure 28
	2			pC max	
Off Isolation	–90			dB typ	$R_L = 50$ Ω , $C_L = 5$ pF, $f = 1$ MHz; see Figure 29
Channel-to-Channel Crosstalk (ADG659)	–90			dB typ	$R_L = 50$ Ω , $C_L = 5$ pF; $f = 1$ MHz; see Figure 31
–3 dB Bandwidth					
ADG658	160			MHz typ	$R_L = 50$ Ω , $C_L = 5$ pF; see Figure 30
ADG659	300			MHz typ	
C_S (OFF)	5			pF typ	$f = 1$ MHz
C_D (OFF)					
ADG658	29			pF typ	$f = 1$ MHz
ADG659	15			pF typ	$f = 1$ MHz

ADG658/ADG659

Parameter	B Version		Y Version	Unit	Test Conditions/Comments
	+25°C	–40°C to +85°C	–40°C to +125°C		
C _D , C _S (ON)					
ADG658	30			pF typ	f = 1 MHz
ADG659	16			pF typ	f = 1 MHz
POWER REQUIREMENTS					V _{DD} = 3.6 V
I _{DD}	0.01		1	μA typ μA max	Digital Inputs = 0 V or 3.6 V

¹ Guaranteed by design; not subject to production test.

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 4.

Parameter	Rating
V_{DD} to V_{SS}	13 V
V_{DD} to GND	$-0.3\text{ V to }+13\text{ V}$
V_{SS} to GND	$+0.3\text{ V to }-6.5\text{ V}$
Analog Inputs ¹	$V_{SS} - 0.3\text{ V to }V_{DD} + 0.3\text{ V}$
Digital Inputs ¹	GND $- 0.3\text{ V to }V_{DD} + 0.3\text{ V}$ or 10 mA, whichever occurs first
Peak Current, S or D (Pulsed at 1 ms, 10% duty cycle max)	40 mA
Continuous Current, S or D	20 mA
Operating Temperature Range	
Automotive (Y Version)	$-40^\circ\text{C to }+125^\circ\text{C}$
Industrial (B Version)	$-40^\circ\text{C to }+85^\circ\text{C}$
Storage Temperature Range	$-65^\circ\text{C to }+150^\circ\text{C}$
Junction Temperature	150°C
θ_{JA} Thermal Impedance	
16-Lead QSOP	104°C/W
16-Lead TSSOP	150.4°C/W
16-Lead LFCSP (4-Layer Board)	70°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec)	215°C
Infrared (15 sec)	220°C
ESD	5.5 kV

¹ Over voltages at A_x , $\overline{EN}$, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device.

Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

ADG658/ADG659

Table 5. ADG658 Truth Table

A2	A1	A0	$\overline{\text{EN}}$	Switch Condition
X ¹	X ¹	X ¹	1	None
0	0	0	0	1
0	0	1	0	2
0	1	0	0	3
0	1	1	0	4
1	0	0	0	5
1	0	1	0	6
1	1	0	0	7
1	1	1	0	8

¹ X = Don't Care

Table 6. ADG659 Truth Table

A1	A0	$\overline{\text{EN}}$	On Switch Pair
X ¹	X ¹	1	None
0	0	0	1
0	1	0	2
1	0	0	3
1	1	0	4

¹ X = Don't Care

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

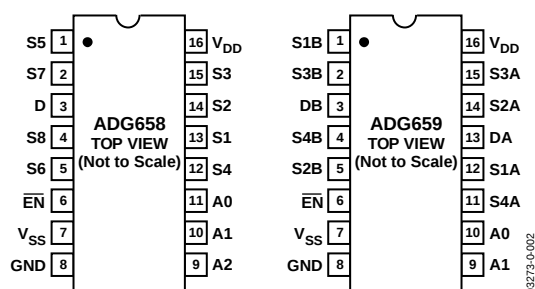


Figure 2. 16-Lead TSSOP/QSOP Pin Configuration

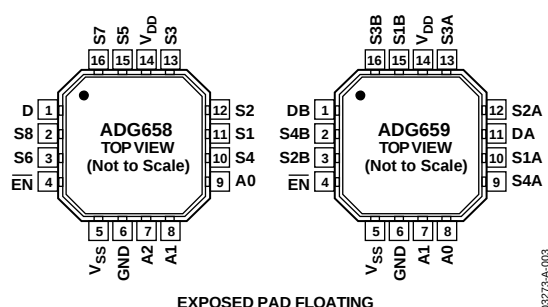


Figure 3. 16-Lead, 4 mm x 4 mm LFCSP Pin Configuration

Table 7. Pin Function Descriptions

Parameter	Description
V_{DD}	Most Positive Power Supply Potential.
V_{SS}	Most Negative Power Supply Potential.
I_{DD}	Positive Supply Current.
I_{SS}	Negative Supply Current.
GND	Ground (0 V) Reference.
S	Source Terminal. May be an input or output.
D	Drain Terminal. May be an input or output.
A_X	Logic Control Input.
EN	Active Low Digital Input. When high, device is disabled and all switches are OFF. When low, A_X logic inputs determine ON switch.
V_D (V_S)	Analog Voltage on Terminals D, S.
R_{ON}	Ohmic Resistance between D and S.
ΔR_{ON}	On Resistance Match between Any Two Channels, i.e., $R_{ONmax} - R_{ONmin}$.
$R_{FLAT(ON)}$	Flatness is defined as the difference between the maximum and minimum value of ON Resistance as measured over the specified analog signal range.
I_S (OFF)	Source Leakage Current with the Switch OFF.
I_D (OFF)	Drain Leakage Current with the Switch OFF.
I_D, I_S (ON)	Channel Leakage Current with the Switch ON.
V_{INL}	Maximum Input Voltage for Logic 0.
V_{INH}	Minimum Input Voltage for Logic 1.
I_{INL} (I_{INH})	Input Current of the Digital Input.
C_S (OFF)	OFF Switch Source Capacitance. Measured with reference to ground.
C_D (OFF)	OFF Switch Drain Capacitance. Measured with reference to ground.
C_D, C_S (ON)	ON Switch Capacitance. Measured with reference to ground.
C_{IN}	Digital Input Capacitance.

ADG658/ADG659

Parameter	Description
t _{ON}	Delay between Applying the Digital Control Input and the Output Switching ON. See Test Circuit 7.
t _{OFF}	Delay between Applying the Digital Control Input and the Output Switching OFF.
t _{BBM}	ON Time. Measured between 80% points of both switches when switching from one address state to another.
Charge Injection	Measure of the Glitch Impulse Transferred from the Digital Input to the Analog Output during Switching.
Off Isolation	Measure of Unwanted Signal Coupling through an OFF Switch.
Crosstalk	Measure of Unwanted Signal Coupled through from One Channel to Another as a Result of Parasitic Capacitance.
Bandwidth	The Frequency at which the Output is Attenuated by 3 dB.
On Response	The Frequency Response of the ON Switch.
Insertion Loss	The Loss Due to the ON Resistance of the Switch.

TYPICAL PERFORMANCE CHARACTERISTICS

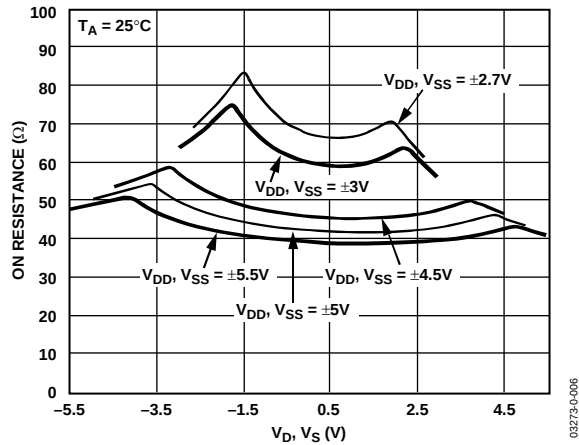


Figure 4. On Resistance vs. V_D (V_S) for Dual Supply

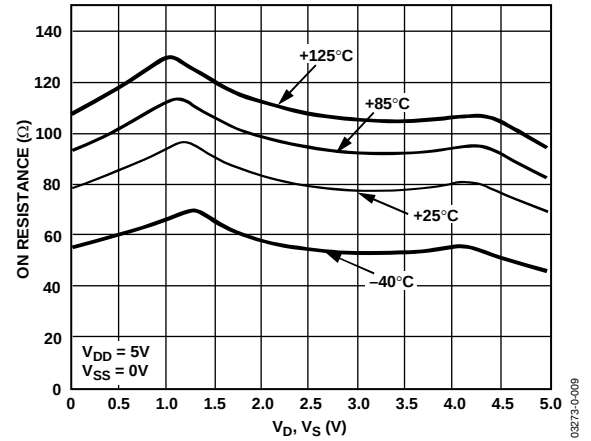


Figure 7. On Resistance vs. V_D (V_S) for Different Temperatures (Single Supply)

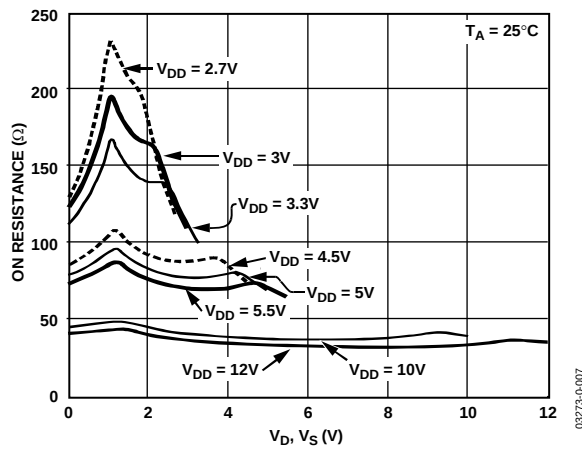


Figure 5. On Resistance vs. V_D (V_S) for Single Supply

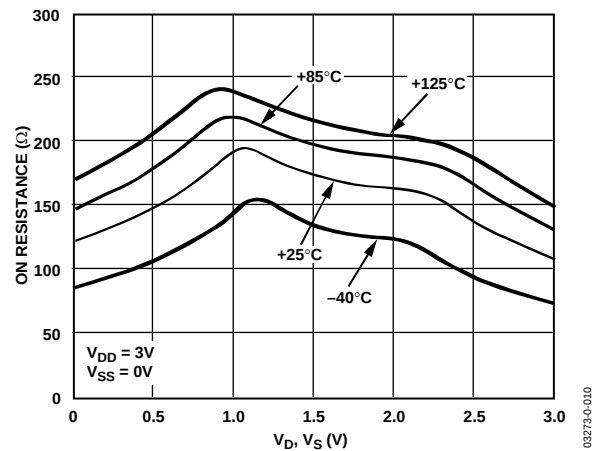


Figure 8. On Resistance vs. V_D (V_S) for Different Temperatures (Single Supply)

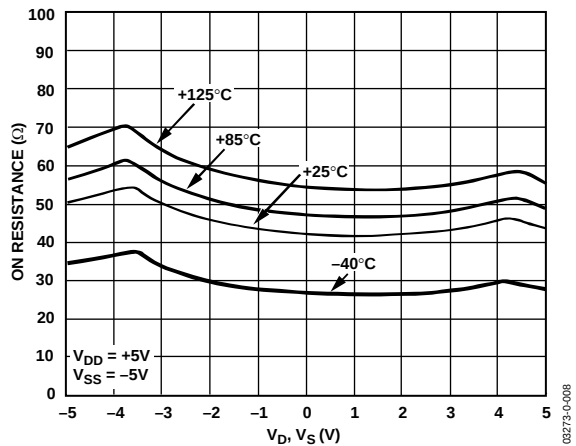


Figure 6. On Resistance vs. V_D (V_S) for Different Temperatures (Dual Supply)

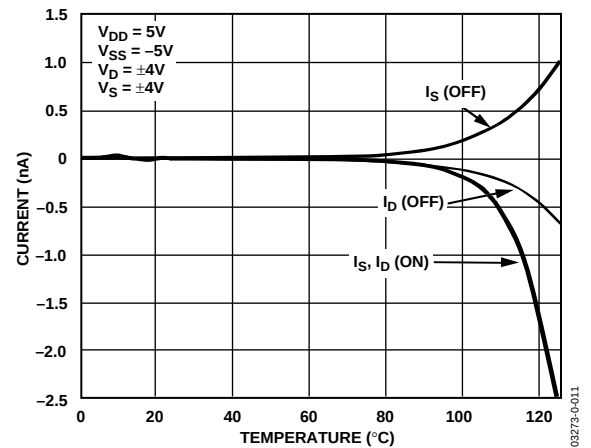


Figure 9. Leakage Current vs. Temperature (Dual Supply)

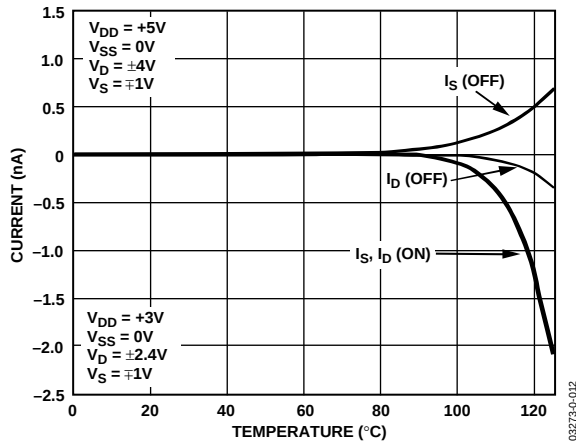


Figure 10. Leakage Current vs. Temperature (Single Supply)

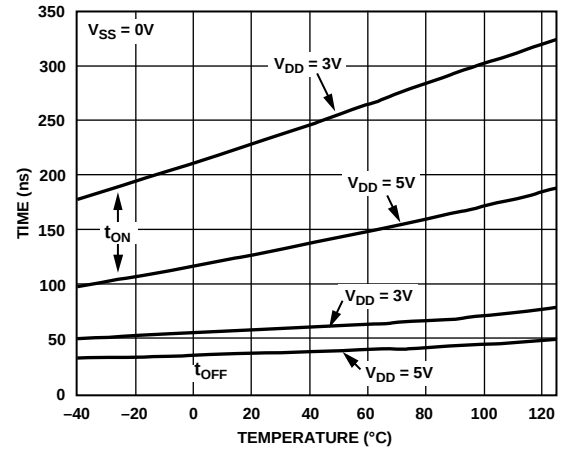


Figure 13. t_{ON}/t_{OFF} Times vs. Temperature (Single Supply)

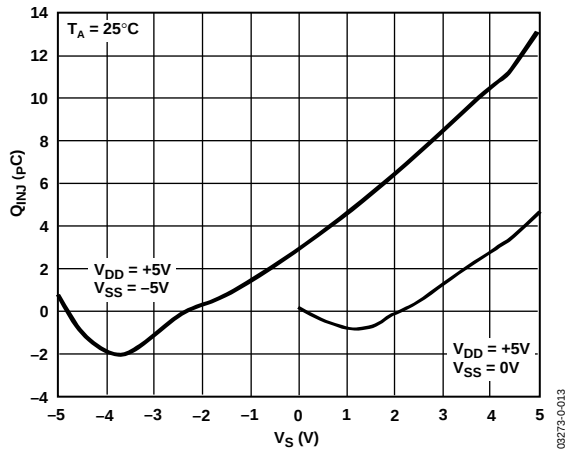


Figure 11. Charge Injection vs. Source Voltage

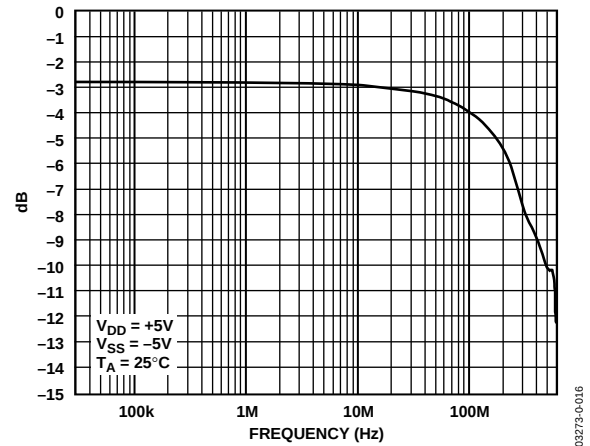


Figure 14. ON Response vs. Frequency (ADG658)

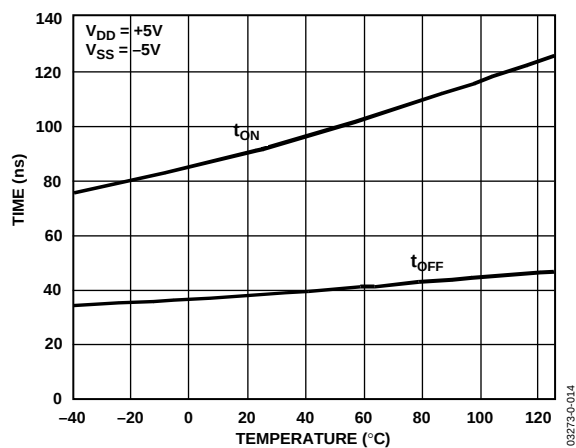


Figure 12. t_{ON}/t_{OFF} Times vs. Temperature (Dual Supply)

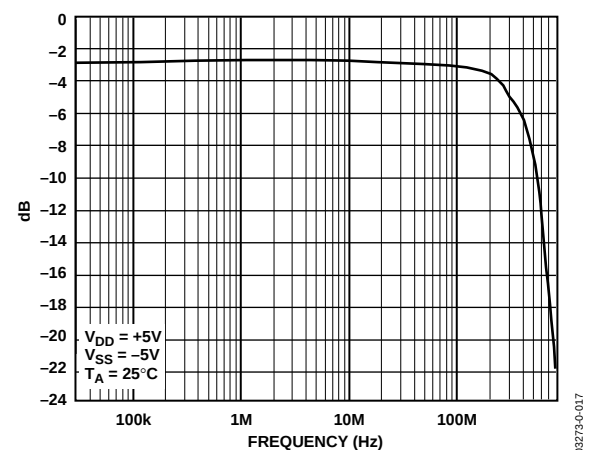


Figure 15. ON Response vs. Frequency (ADG659)

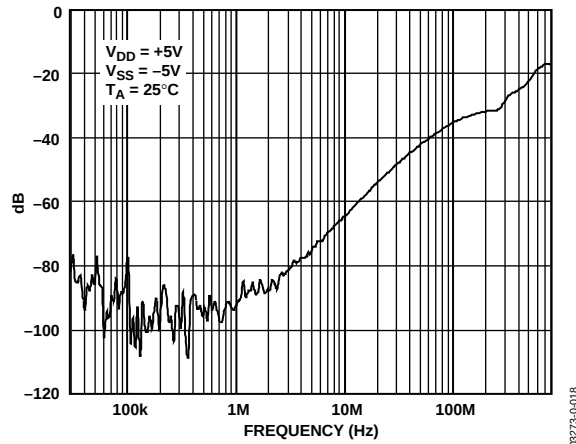


Figure 16. OFF Isolation vs. Frequency

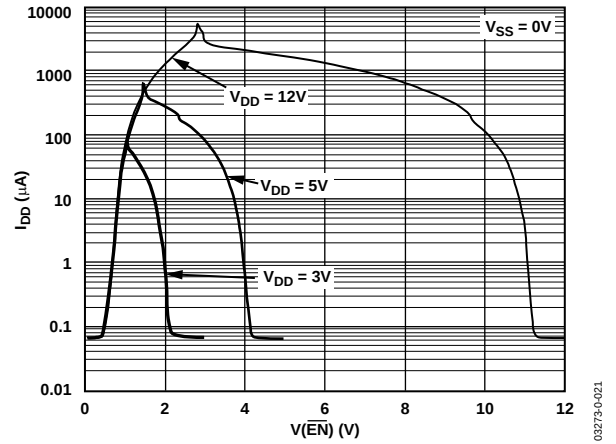


Figure 19. V_{DD} Current vs. Logic Level

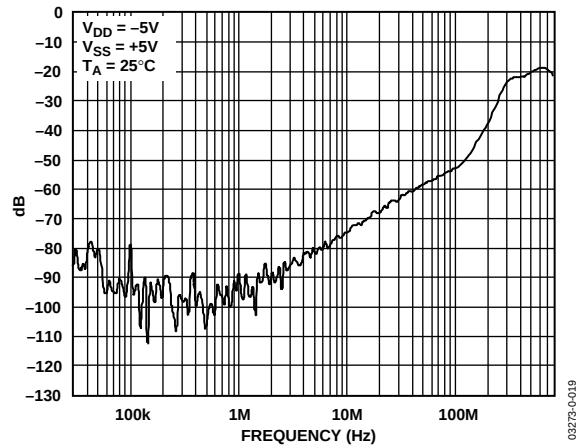


Figure 17. Crosstalk vs. Frequency

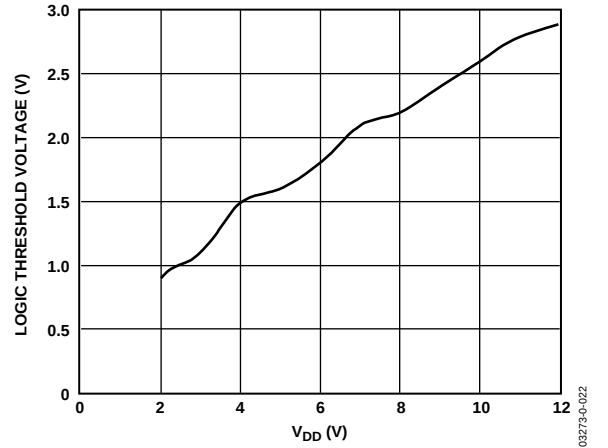


Figure 20. Logic Threshold Voltage vs. Supply Voltage

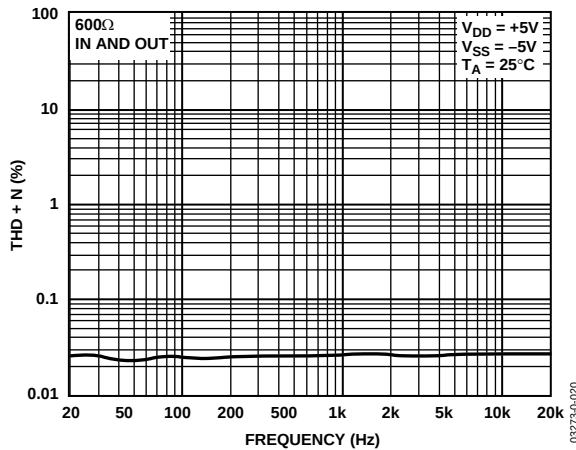


Figure 18. THD + Noise

TEST CIRCUITS

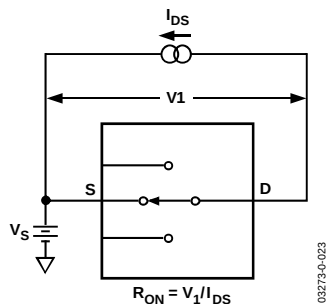


Figure 21. ON Resistance

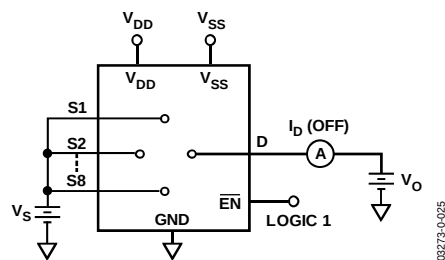


Figure 23. I_D (OFF)

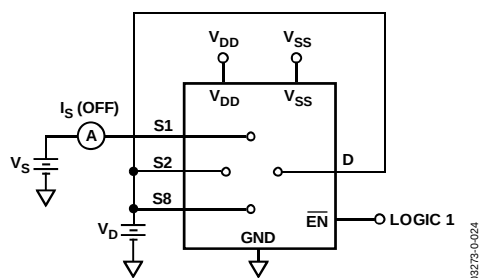


Figure 22. I_S (OFF)

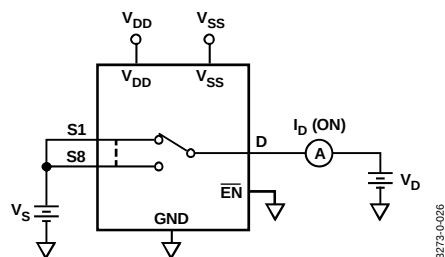


Figure 24. I_D (ON)

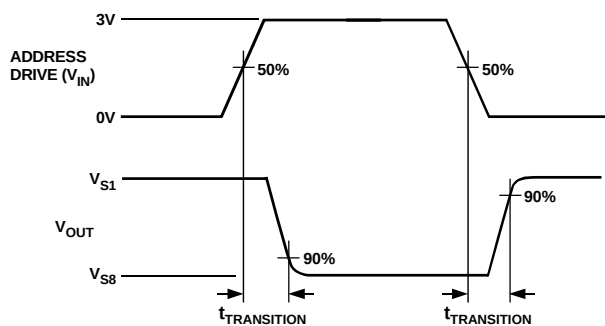
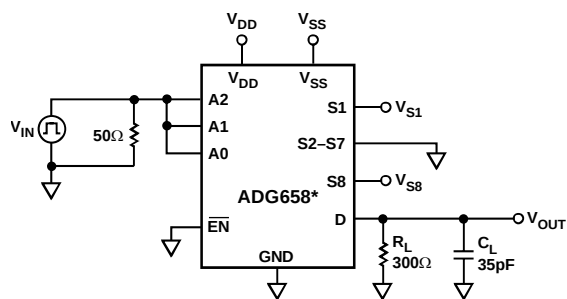
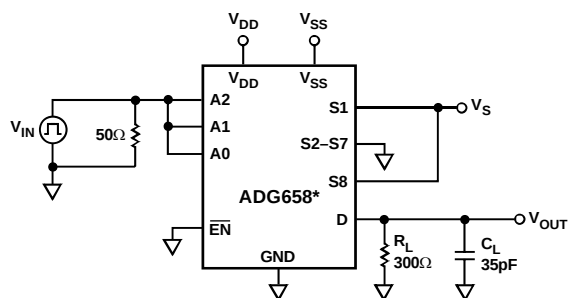
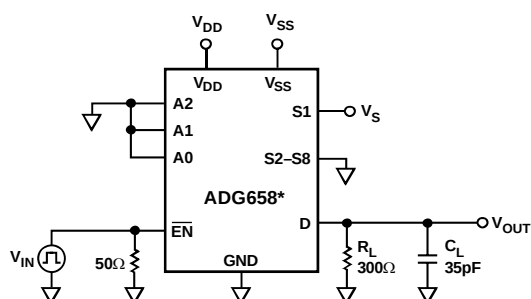


Figure 25. Switching Time of Multiplexer, $t_{\text{TRANSITION}}$



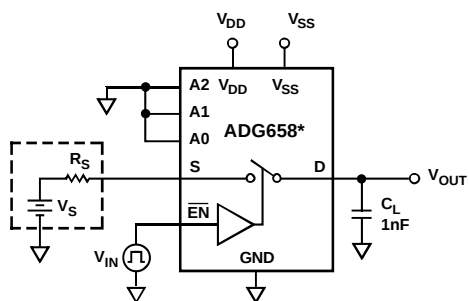
*SIMILAR CONNECTION FOR ADG659

Figure 26. Break-Before-Make Delay, t_{BBM}



*SIMILAR CONNECTION FOR ADG659

Figure 27. Enable Delay, $t_{ON}(\overline{EN})$, $t_{OFF}(\overline{EN})$



*SIMILAR CONNECTION FOR ADG659

Figure 28. Charge Injection

ADG658/ADG659

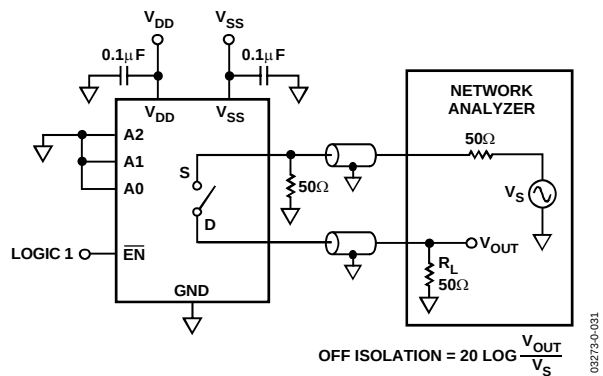


Figure 29. Off Isolation

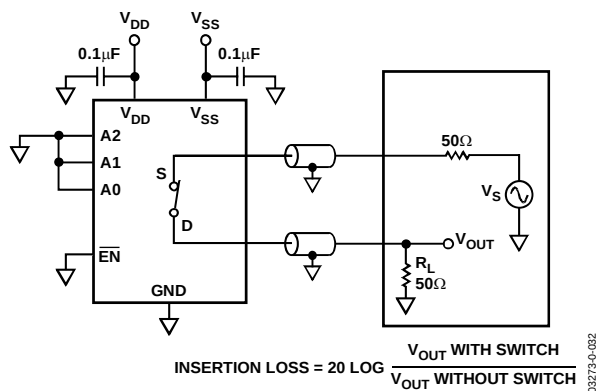


Figure 30. Bandwidth

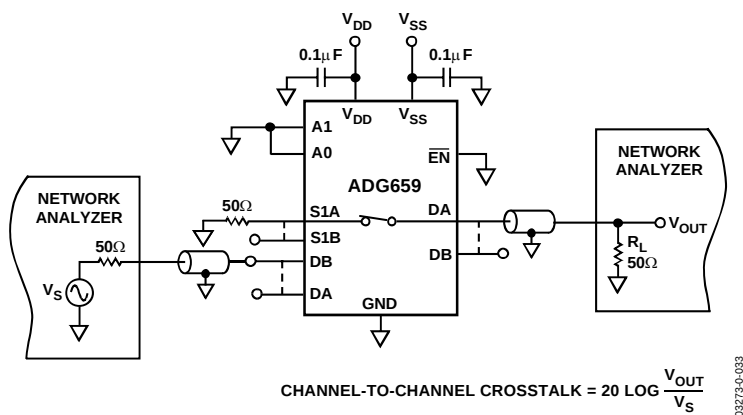


Figure 31. Channel-to-Channel Crosstalk

OUTLINE DIMENSIONS

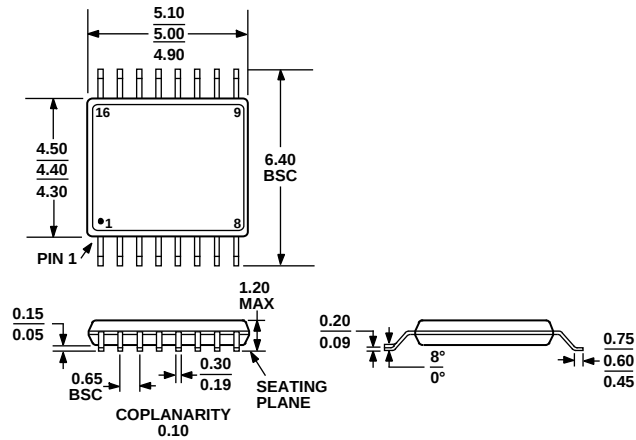


Figure 32. 16-Lead Thin Shrink Small Outline Package [TSSOP]
(RU-16)
Dimensions shown in millimeters

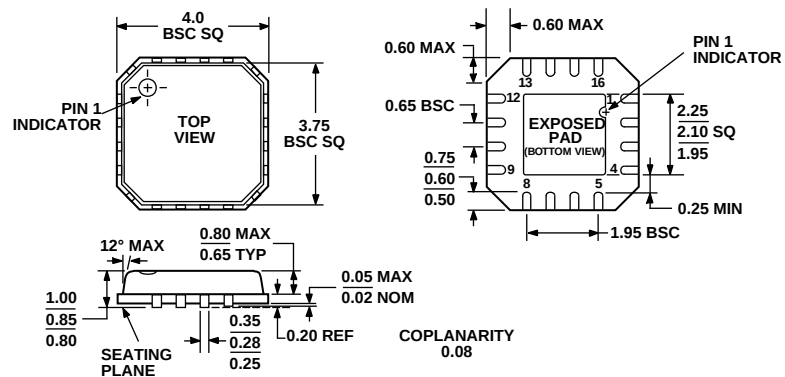


Figure 33. 16-Lead Lead Frame Chip Scale Package [LFCSP]
(CP-16-4)
Dimensions shown in millimeters

ADG658/ADG659

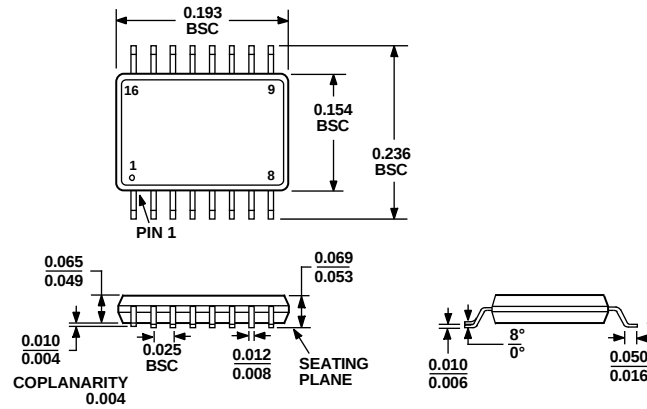


Figure 34. 16-Lead Shrink Small Outline Package [QSOP]
(RQ-16)
Dimensions shown in millimeters

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
ADG658YRU	−40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG658YRU-REEL7	−40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG658YRUZ ¹	−40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG658YRUZ-REEL7 ¹	−40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG658YCP	−40°C to +85°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16
ADG658YCP-REEL7	−40°C to +85°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16
ADG658YCPZ ¹	−40°C to +85°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16
ADG658YRQ	−40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG658YRQ-REEL	−40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG658YRQZ ¹	−40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG658YRQZ-REEL7 ¹	−40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG659YRU	−40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG659YRU-REEL7	−40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG659YRUZ ¹	−40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG659YRUZ-REEL7 ¹	−40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG659WYRUZ-REEL7 ^{1, 2}	−40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG659YCP	−40°C to +85°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16
ADG659YCPZ ¹	−40°C to +85°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16
ADG659YCPZ-REEL7 ¹	−40°C to +85°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16
ADG659YRQ	−40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG659YRQ-REEL	−40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG659YRQ-REEL7	−40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG659YRQZ ¹	−40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16

¹ Z = RoHS Compliant Part.

² Qualified for automotive.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

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moschip.ru_6

moschip.ru_9